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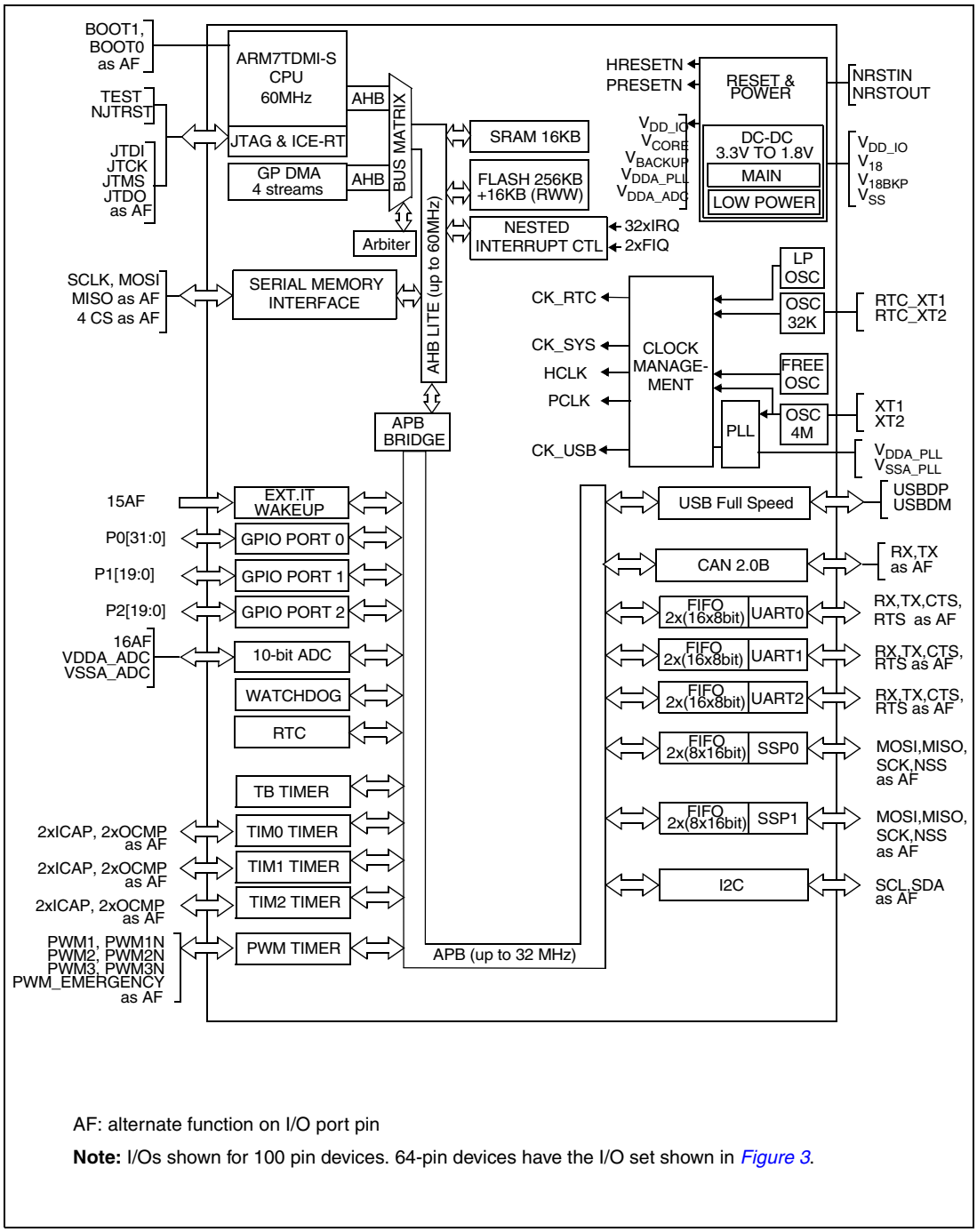
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	60MHz
Connectivity	I²C, SPI, SSI, SSP, UART/USART
Peripherals	DMA, PWM, WDT
Number of I/O	38
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 11x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str755fr2t6

3.2 Block diagram

Figure 1. STR750 block diagram

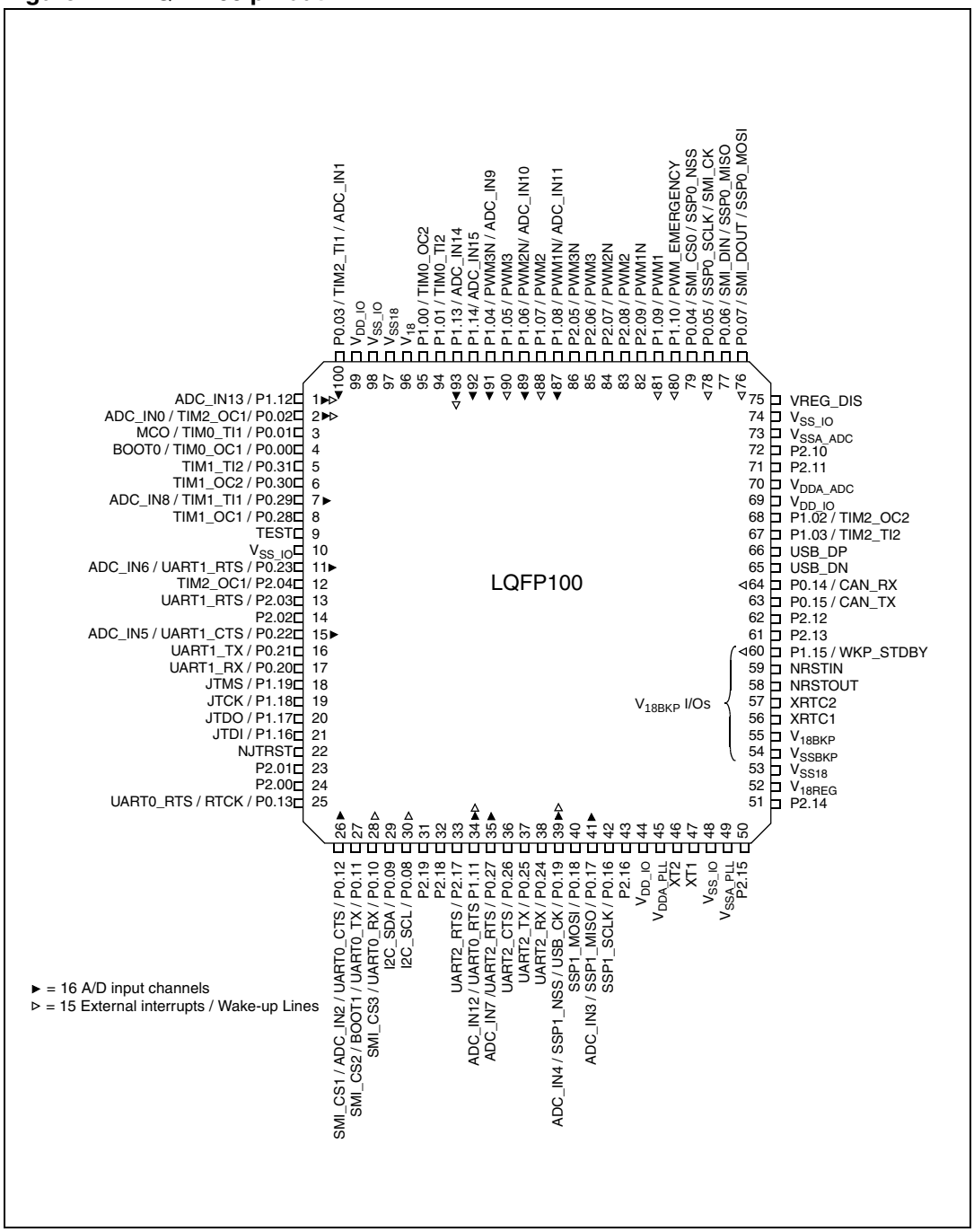


AF: alternate function on I/O port pin

Note: I/Os shown for 100 pin devices. 64-pin devices have the I/O set shown in *Figure 3*.

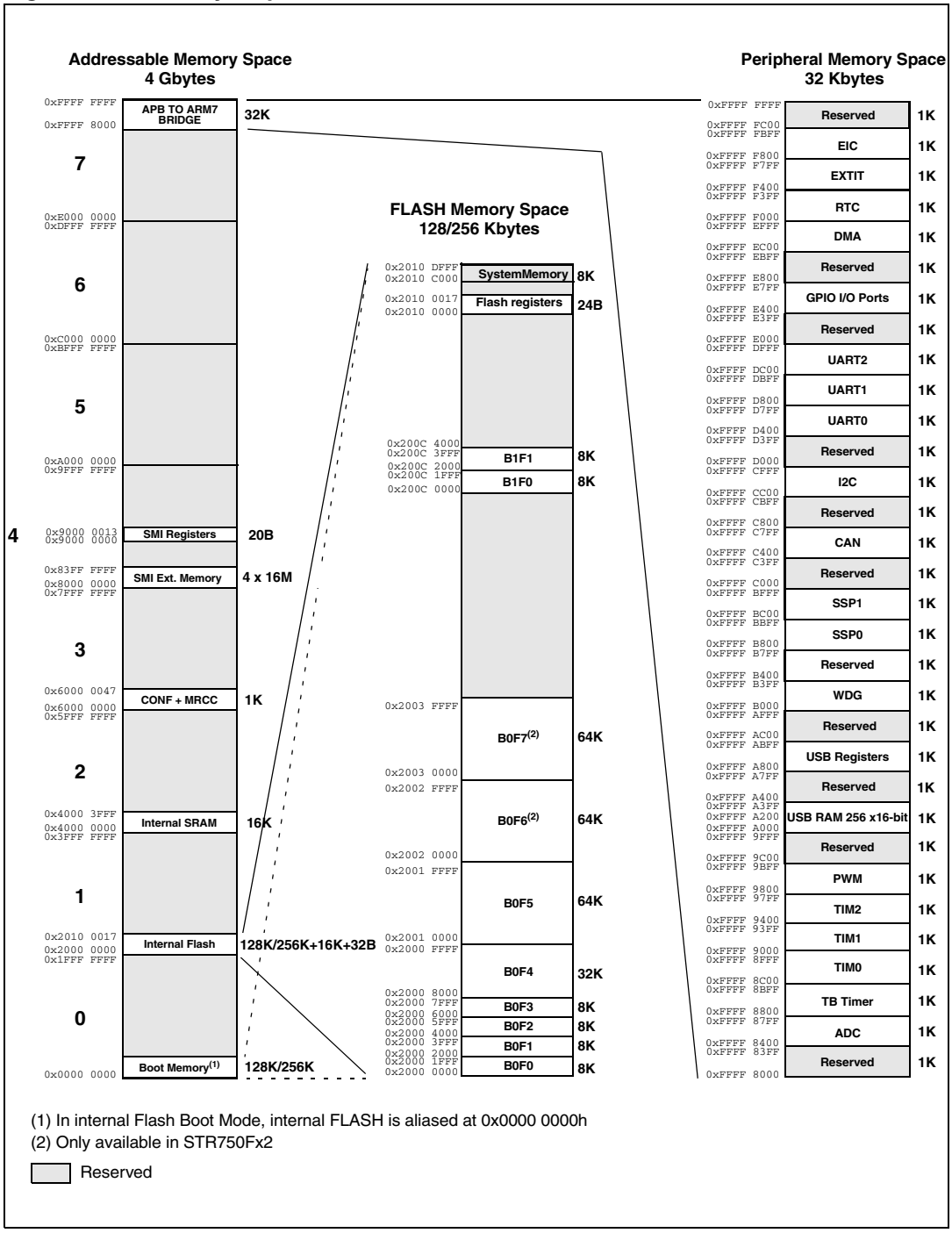
4 Pin description

Figure 2. LQFP100 pinout



5 Memory map

Figure 5. Memory map



(1) In internal Flash Boot Mode, internal FLASH is aliased at 0x0000 0000h
(2) Only available in STR750Fx2

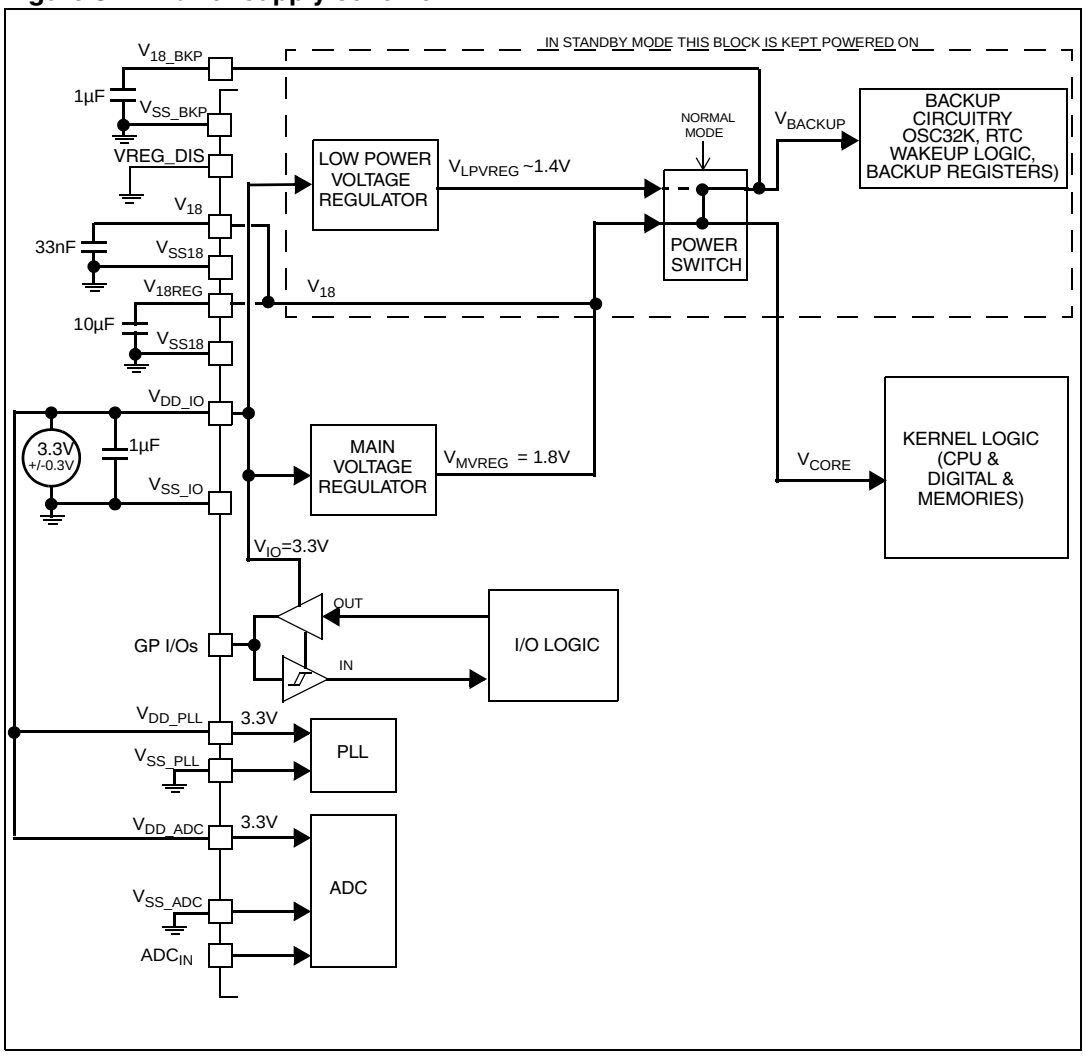
Reserved

6.1.6 Power supply schemes

When mentioned, some electrical parameters can refer to a dedicated power scheme among the four possibilities. The four different power schemes are described below.

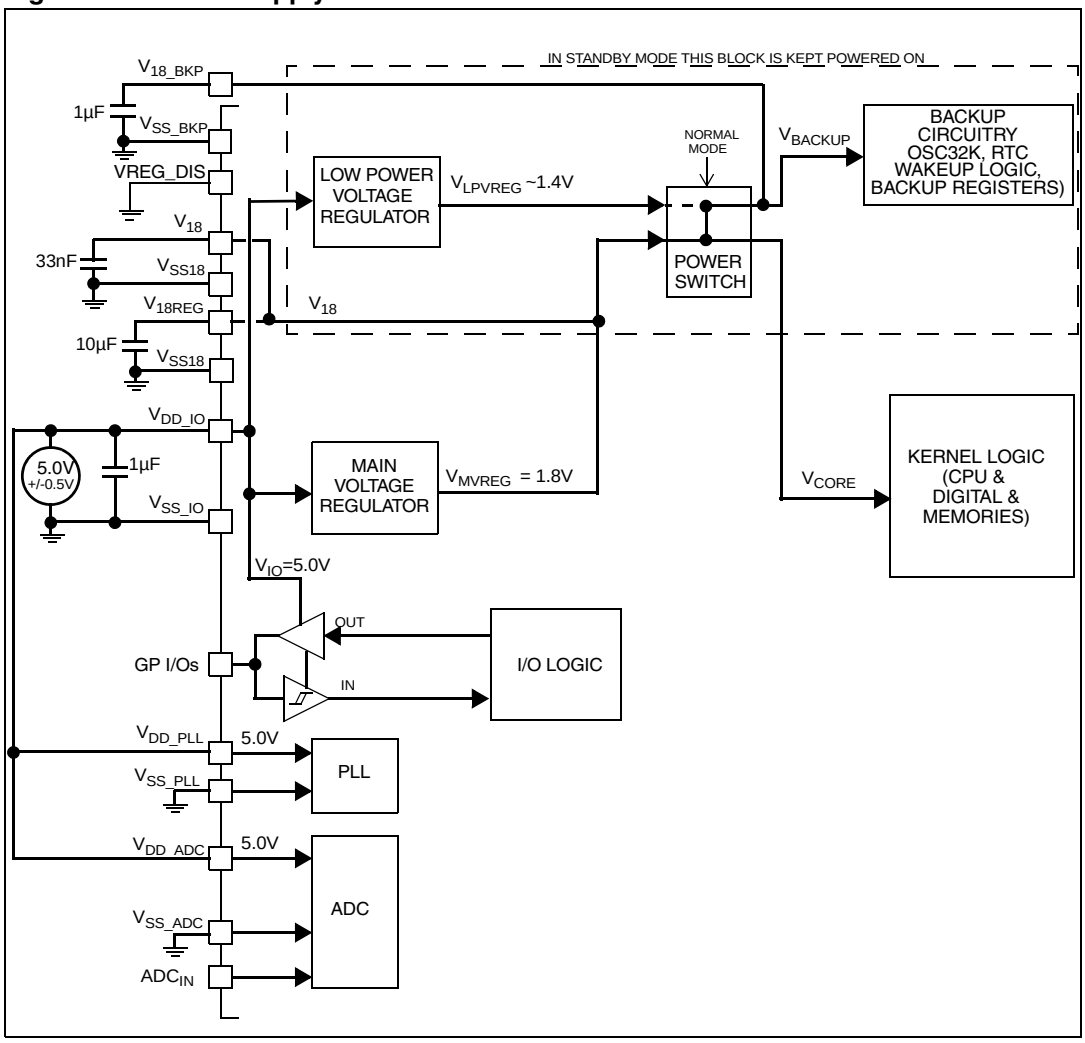
Power supply scheme 1: Single external 3.3 V power source

Figure 8. Power supply scheme 1



Power supply scheme 3: Single external 5 V power source

Figure 10. Power supply scheme 3



6.3.2 Operating conditions at power-up / power-down

Subject to general operating conditions for T_A.

Table 11. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{VDD_IO}	V_{DD_IO} rise time rate		20			µs/V
					20	ms/V
t_{V18}	V_{18} rise time rate (1)	When 1.8 V power is supplied externally	20			µs/V
					20	ms/V

1. Data guaranteed by characterization, not tested in production.

6.3.3 Embedded voltage regulators

Subject to general operating conditions for V_{DD_IO}, and T_A

Table 12. Embedded voltage regulators

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{MVREG}	MVREG power supply(1)	load <150 mA	1.65	1.80	1.95	V
V_{LPVREG}	LPVREG power supply(2)	load <10 mA	1.30	1.40	1.50	V
t_{VREG_PWRUP}(1)	Voltage Regulators start-up time (to reach 90% of final V_{18} value) at V_{DD_IO} power-up(3)	V_{DD_IO} rise slope = 20 µs/V		80		µs
		V_{DD_IO} rise slope = 20 ms/V		35		ms

1. V_{MVREG} is observed on the V_{18}, V_{18REG} and V_{18BKP} pins except in the following case:
   - In STOP mode with MVREG OFF (LP_PARAM13 bit). See note 2.
   - In STANDBY mo*de. See note 2.*
2. In STANDBY mode, V_{LPVREG} is observed on the V_{18BKP} pin
   In STOP mode, V_{LPVREG} is observed on the V_{18}, V_{18REG} and V_{18BKP} pins.
3. Once V_{DD_IO} has reached 3.0 V, the RSM (Regulator Startup Monitor) generates an internal RESET during this start-up time.

6.3.4 Supply current characteristics

The current consumption is measured as described in *Figure 12 on page 30* and *Figure 13 on page 30*.

Subject to general operating conditions for V_{DD_IO}, and T_A

Maximum power consumption

For the measurements in *Table 13* and *Table 14*, the MCU is placed under the following conditions:

- All I/O pins are configured in output push-pull 0
- All peripherals are disabled except if explicitly mentioned.
- Embedded Regulators are used to provide 1.8 V (except if explicitly mentioned).

Table 13. Maximum power consumption in RUN and WFI modes

Symbol	Parameter	Conditions (1)		Typ (2)	Max (3)	Unit
I_{DD}	Supply current in RUN mode	External Clock with PLL multiplication, code running from RAM, all peripherals enabled in the MRCC_PLCKEN register: f_{HCLK}=60 MHz, f_{PCLK}=30 MHz Single supply scheme see *Figure 12* / *Figure 14*	3.3V and 5V range	80	90	mA
	Supply current in WFI mode	External Clock, code running from RAM: f_{HCLK}=60 MHz, f_{PCLK}=30 MHz Single supply scheme see *Figure 12*./ *Figure 14* Parameter setting BURST=1, WFI_FLASHEN=1	3.3V and 5V range	62	67	mA

1. The conditions for these consumption measurements are described at the beginning of *Section 6.3.4*.
2. Typical data are based on T_A=25°C, V_{DD_IO}=3.3V or 5.0V and V_{18}=1.8V unless otherwise specified.
3. Data based on product characterisation, tested in production at V_{DD_IO} max and V_{18} max (1.95V in dual supply mode or regulator output value in single supply mode) and T_A max.

Table 14. Maximum power consumption in STOP and STANDBY modes

Symbol	Parameter	Conditions[1]		Typ[2]	Max[3]			Unit
					T_A 25°C	T_A 85°C	T_A 105°C	
I_{DD}	Supply current in STOP mode	LP_PARAM bits: ALL OFF[4] Single supply scheme see *Figure 12*.	3.3V range	12	16	117	250	µA
		LP_PARAM bits: ALL OFF Dual supply scheme see *Figure 13*.	I_{DD_V18} I_{DD_V33}	5 <1	8 3	60 20	110 26	µA
		LP_PARAM bits: ALL OFF[4] Single supply scheme see *Figure 10*	5V range	15	22	160	310	µA
		LP_PARAM bits: ALL OFF Dual supply scheme see *Figure 11*	I_{DD_V18} I_{DD_V50}	5 3	8 6	60 50	110 65	µA
	Supply current in STANDBY mode	RTC OFF	3.3 V range	10	20	25	28	
			5V range	15	25	30	33	

1. The conditions for these consumption measurements are described at the beginning of *Section 6.3.4*.
2. Typical data are based on T_A=25°C, V_{DD_IO}=3.3V or 5.0V and V_{18}=1.8V unless otherwise specified.
3. Data based on product characterisation, tested in production at V_{DD_IO} max and V_{18} max (1.95V in dual supply mode or regulator output value in single supply mode).
4. In this mode, the whole digital circuitry is powered internally by the LPVREG at approximately 1.4V, which significantly reduces the leakage currents.

Table 16. Dual supply supply typical power consumption in Run, WFI, Slow and Slow-WFI modes

To calculate the power consumption in Dual supply mode, refer to the values given in *Table 15*. and consider that this consumption is split as follows:

$I_{DD(single\ supply)} \sim I_{DD(dual\ supply)} = I_{DD\_V18} + I_{DD(VDD\_IO)}$

For 3.3V range: $I_{DD(VDD\_IO)}$ ~ 1 to 2 mA

For 5V range: $I_{DD(VDD\_IO)}$ ~ 2 to 3 mA

Therefore most of the consumption is sunk on the V_{18} power supply

This formula does not apply in STOP and STANDBY modes, refer to *Table 17*.

Subject to general operating conditions for V_{DD_IO}, and T_A

Table 17. Typical power consumption in STOP and STANDBY modes

Symbol	Parameter	Conditions		3.3V Typ(1)	5V Typ(2)	Unit
I_{DD}(3)	Supply current in STOP mode(4)	LP_PARAM bits: ALL OFF(5)		12	15	µA
		LP_PARAM bits : MVREG ON, OSC4M OFF, FLASH OFF(6)		130	135	
		LP_PARAM bits: MVREG ON, OSC4M ON , FLASH OFF(6)		1950	1930	
		LP_PARAM bits: MVREG ON, OSC4M OFF, FLASH ON (6)		630	635	
		LP_PARAM bits: MVREG ON, OSC4M ON, FLASH ON (6)		2435	2425	
	Supply current in STOP mode(7)	LPPARAM bits: ALL OFF, with V_{18}=1.8 V	I_{DD_V18} I_{DD_V33}	5 <1	5 <1	µA
		LP_PARAM bits: OSC4M ON, FLASH OFF	I_{DD_V18} I_{DD_V33}	410 1475	410 1435	
		LP_PARAM bits: OSC4M OFF, FLASH ON	I_{DD_V18} I_{DD_V33}	550 <1	550 1	
		LP_PARAM bits: OSC4M ON, FLASH ON	I_{DD_V18} I_{DD_V33}	910 1475	910 1445	
	Supply current in STANDBY mode(4)	RTC OFF		11	14	µA
		RTC ON clocked by OSC32K		14	18	

1. Typical data are based on T_A=25°C, V_{DD_IO}=3.3 V and V_{18}=1.8 V unless otherwise indicated in the table.
2. Typical data are based on T_A=25°C, V_{DD_IO}=5.0 V and V_{18}=1.8 V unless otherwise indicated in the table.
3. The conditions for these consumption measurements are described at the beginning of *Section 6.3.4 on page 36*.
4. Single supply scheme see *Figure 12*.
5. In this mode, the whole digital circuitry is powered internally by the LPVREG at approximately 1.4 V, which significantly reduces the leakage currents.
6. In this mode, the whole digital circuitry is powered internally by the MVREG at 1.8 V.
7. Dual supply scheme see *Figure 13*.

Supply and clock manager power consumption

Table 18. Supply and clock manager power consumption

Symbol	Parameter	Conditions[1]	3.3V Typ	5V Typ	Unit
$I_{DD(OSC4M)}$	Supply current of resonator oscillator in STOP or WFI mode (LP_PARAM bit: OSC4M ON)	External components specified in: *4/8 MHz crystal / ceramic resonator oscillator (XT1/XT2) on page 46*	1815	1795	µA
$I_{DD(FLASH)}$	FLASH static current consumption in STOP or WFI mode (LP_PARAM bit FLASH ON)		515	515	
$I_{DD(MVREG)}$	Main Voltage Regulator static current consumption in STOP mode (LP_PARAM bit: MVREG ON)		130	135	
$I_{DD(LPVREG)}$	Low Power Voltage Regulator + RSM current static current consumption	STOP mode includes leakage where V_{18} is internally set to 1.4 V	12	15	
		STANDBY mode where V_{18BKP} and V_{18} are internally set to 1.4 V and 0 V respectively	11	14	

1. Measurements performed in 3.3V single supply mode see *Figure 12*

6.3.5 Clock and timing characteristics

XT1 external clock source

Subject to general operating conditions for V_{DD_IO}, and T_A.

Table 20. XT1 external clock source

Symbol	Parameter	Conditions(1) (2)	Min	Typ	Max	Unit
f_{XT1}	External clock source frequency	see *Figure 20*		4	60	MHz
V_{XT1H}	XT1 input pin high level voltage		$0.7xV_{DD\_IO}$		V_{DD_IO}	V
V_{XT1L}	XT1 input pin low level voltage		V_{SS}		$0.3xV_{DD\_IO}$	
$t_{w(XT1H)}$ $t_{w(XT1L)}$	XT1 high or low time (3)		6			ns
$t_{r(XT1)}$ $t_{f(XT1)}$	XT1 rise or fall time (3)				20	
I_L	XTx Input leakage current	$V_{SS} \le V_{IN} \le V_{DD\_IO}$			±1	µA
$C_{IN(XT1)}$	XT1 input capacitance(3)			5		pF
$DuCy_{(XT1)}$	Duty cycle		45		55	%

1. Data based on typical application software.
2. Time measured between interrupt event and interrupt vector fetch. $\Delta t_{c(INST)}$ is the number of t_{CPU} cycles needed to finish the current instruction execution.
3. Data based on design simulation and/or technology characteristics, not tested in production.

4/8 MHz crystal / ceramic resonator oscillator (XT1/XT2)

The STR750 system clock or the input of the PLL can be supplied by a OSC4M which is a 4 MHz clock generated from a 4 MHz or 8 MHz crystal or ceramic resonator. If using an 8 MHz oscillator, software set the XTDIV bit to enable a divider by 2 and generate a 4 MHz OSC4M clock. All the information given in this paragraph are based on product characterisation with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and start-up stabilization time. Refer to the crystal/ceramic resonator manufacturer for more details (frequency, package, accuracy...).

Table 22. 4/8 MHz crystal / ceramic resonator oscillator (XT1/XT2)(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC4M}	Oscillator frequency	4 MHz Crystal/Resonator Oscillator connected on XT1/XT2 XTDIV=0 or 8 MHz Crystal/Resonator Oscillator connected on XT1/XT2 XTDIV=1		4		MHz
R_F	Feedback resistor		200	240	270	kΩ
C_{L1}(2) C_{L2}	Recommended load capacitance versus equivalent serial resistance of the crystal or ceramic resonator (R_S)(3)	R_S=200Ω			60	pF
i_2	XT2 driving current	V_{DD_IO}=3.3 V or 5.0 V		425		µA
$t_{SU(OSC4M)}$(4)	Startup time at V_{DD_IO} power-up			1		ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. For C_{L1} and C_{L2} it is recommended to use high-quality ceramic capacitors in the 5-pF to 25-pF range (typ.) designed for high-frequency applications and selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2}, are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included when sizing C_{L1} and C_{L2} (10 pF can be used as a rough estimate of the combined pin and board capacitance).
3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
4. $t_{SU(OSC4M)}$ is the typical start-up time measured from the moment V_{DD_IO} is powered (with a quick V_{DD_IO} ramp-up from 0 to 3.3V (<50µs) to a stabilized 4MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal/ceramic resonator manufacturer.

Figure 21. Typical application with a 4 or 8 MHz crystal or ceramic resonator

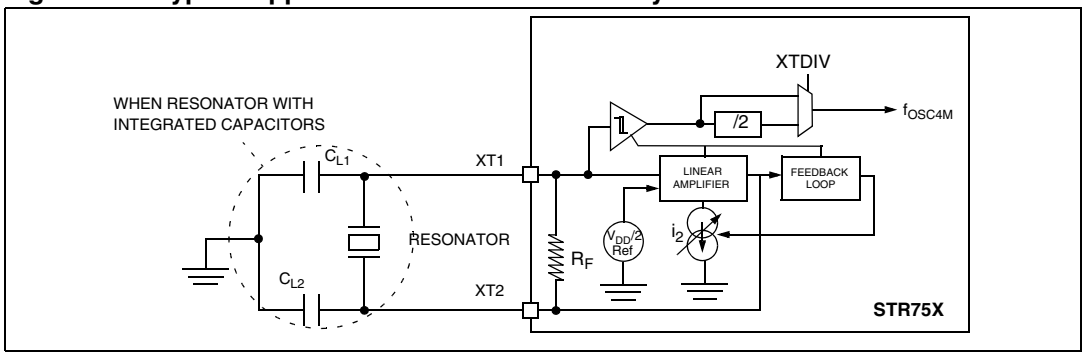


Table 37. PWM Timer (PWM)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{res(PWM)}$	PWM resolution time	$f_{CK\_TIM(MAX)} = f_{CK\_SYS}$	1			t_{CK_TIM}
		$f_{CK\_TIM} = f_{CK\_SYS}$ = 60 MHz	16.6(1)			ns
Res_{PWM}	PWM resolution				16	bit
V_{OS}(1)	PWM/DAC output step voltage	V_{DD_IO}=3.3 V, Res=16-bits		50(1)		µV
		V_{DD_IO}=5.0 V, Res=16-bits		76(1)		µV
$t_{COUNTER}$	Timer clock period when internal clock is selected		1		65536	t_{CK_TIM}
		f_{CK_TIM}=60 MHz	0.0166		1087	µs
t_{MAX_COUNT}	Maximum Possible Count				65536x 65536	t_{CK_TIM}
		$f_{CK\_TIM} = f_{CK\_SYS}$ = 60 MHz			71.58	s

1. Take into account the frequency limitation due to the I/O speed capability when outputting the PWM to an I/O pin, as described in *: Output speed on page 57*.

6.3.10 Communication interface characteristics

SSP synchronous serial peripheral in master mode (SPI or TI mode)

General operating conditions: V_{33}, 3.0V to 3.3V, V18 =1.8V, $C_L \approx 45$ pF.

Table 38. SSP master mode characteristics(1)

Symbol	Parameter	Conditions		Min	Max	Unit
f_{SCK}	SPI clock frequency(2)		SSP0		16	MHz
			SSP1		8	
$t_{r(SCK)}$	SPI clock rise time		SSP0		14	ns
			SSP1		33	
$t_{f(SCK)}$	SPI clock fall time		SSP0		11	
			SSP1		30	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time		SSP0		19	
			SSP1		30	
t_{NSSLQV}	NSS low to Data Output MOSI valid time		SSP0		$0.5t_{SCK}$+15ns	
			SSP1		$0.5t_{SCK}$+30ns	
$t_{SCKNSSH}$	SCK last edge to NSS high	CPHA = 0	SSP0		$0.5t_{SCK}$+15ns	
			SSP1		$0.5t_{SCK}$+30ns	
		CPHA = 1	SSP0		t_{SCK}+15ns	
			SSP1		t_{SCK}+30ns	
t_{SCKQV}	SCK trigger edge to data output MOSI valid time		SSP0		15	
			SSP1		30	
t_{SCKQX}	SCK trigger edge to data output MOSI invalid time		SSP0	0		
			SSP1	0		
t_{su}	Data input (MISO) setup time w.r.t SCK sampling edge		SSP0	25		
			SSP1	25		
t_h	Data input (MISO) hold time w.r.t SCK sampling edge		SSP0	0		
			SSP1	0		

1. Data based on characterisation results, not tested in production.
2. Max frequency for the 2 SSPs is $f_{PCLK}/2$; f_{PCLK} max = 32 MHz. This takes into account the frequency limitation due to I/O speed capability. SSP0 uses IO4 type while SSP1 uses IO2 type I/Os.

Figure 34. SPI configuration - slave mode with CPHA=0, continuous transfer

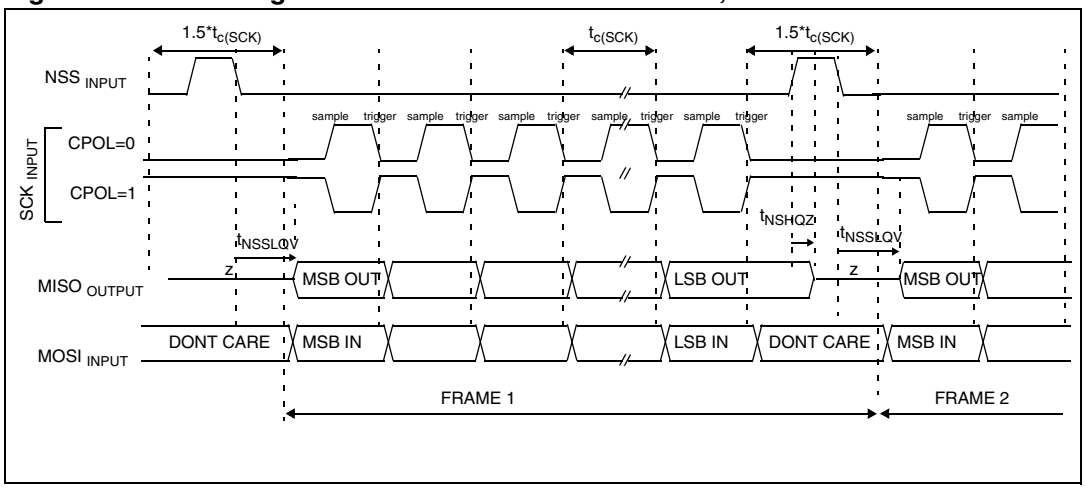


Figure 35. SPI configuration, slave mode with CPHA=1, single transfer

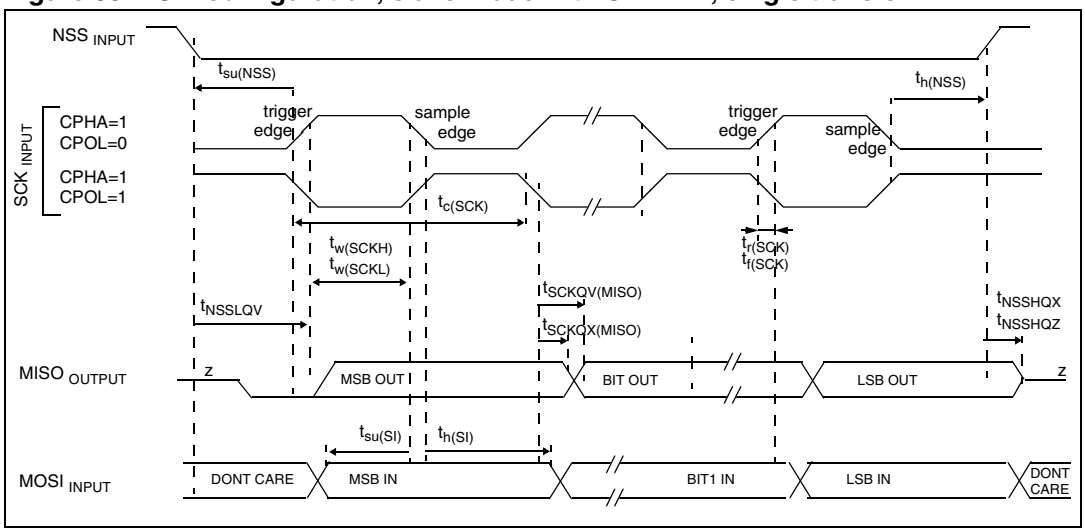
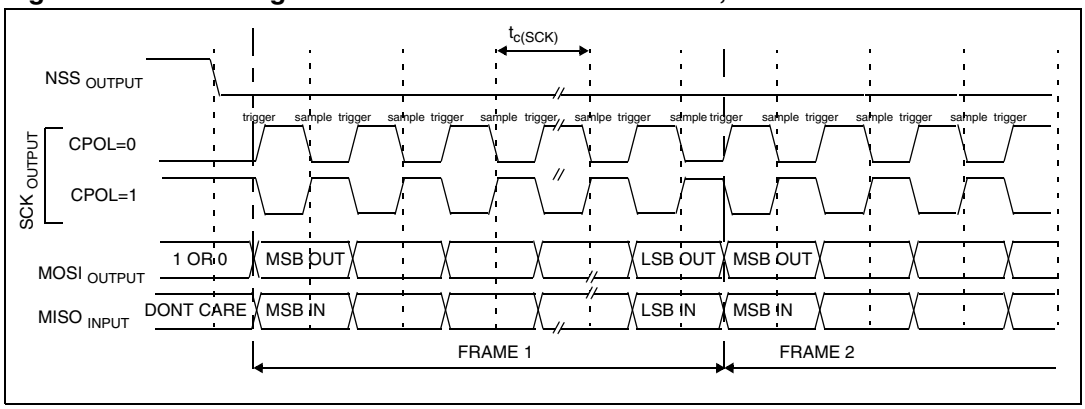


Figure 36. SPI configuration - slave mode with CPHA=1, continuous transfer



SMI - serial memory interface

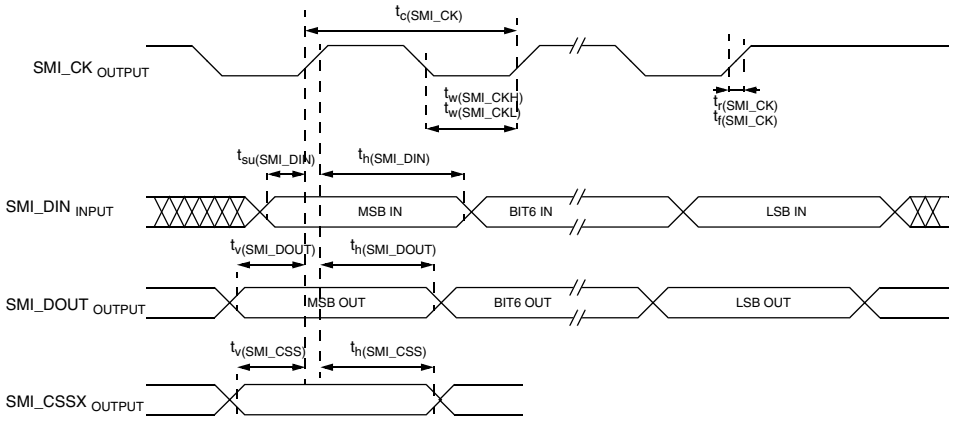
Subject to general operating conditions with $C_L \approx 30$ pF.

Table 40. SMI characteristics(1)

Symbol	Parameter	Min	Max	Unit
f_{SMI_CK}	SMI clock frequency		32(2)(3)	MHz
			48(4)	
$t_{r(SMI\_CK)}$	SMI clock rise time		10	ns
$t_{f(SMI\_CK)}$	SMI clock fall time		8	
$t_{v(SMI\_DOUT)}$	Data output valid time		10	
$t_{h(SMI\_DOUT)}$	Data output hold time		0	
$t_{v(SMI\_CSSx)}$	CSS output valid time		10	
$t_{h(SMI\_CSSx)}$	CSS output hold time		0	
$t_{su(SMI\_DIN)}$	Data input setup time	0		
$t_{h(SMI\_DIN)}$	Data input hold time	5		

1. Data based on characterisation results, not tested in production.
2. Max. frequency = $f_{PCLK}/2 = 64/2 = 32$ MHz.
3. Valid for all temperature ranges: -40 to 105 °C, with 30 pF load capacitance.
4. Valid up to 60 °C, with 10 pF load capacitance.

Figure 39. SMI timing diagram



I²C - Inter IC control interface

Subject to general operating conditions for V_{DD_IO}, f_{PCLK}, and T_A unless otherwise specified.

The I²C interface meets the requirements of the Standard I²C communication protocol described in the following table with the restriction mentioned below:

Restriction: The I/O pins which SDA and SCL are mapped to are not “True” Open-Drain: when configured as open-drain, the PMOS connected between the I/O pin and V_{DD_IO} is disabled, but it is still present. Also, there is a protection diode between the I/O pin and V_{DD_IO}. Consequently, when using this I²C in a multi-master network, it is

6.3.11 USB characteristics

The USB interface is USB-IF certified (Full Speed).

Table 42. USB startup time

Symbol	Parameter	Conditions	Max	Unit
$t_{STARTUP}$	USB transceiver startup time		1	µs

Table 43. USB characteristics

USB DC Electrical Characteristics					
Symbol	**Parameter**	**Conditions**	**Min.(1)(2)**	**Max.(1)(2)**	**Unit**
Input Levels					
V_{DI}	Differential Input Sensitivity	I(DP, DM)	0.2		V
V_{CM}	Differential Common Mode Range	Includes V_{DI} range	0.8	2.5	
V_{SE}	Single Ended Receiver Threshold		1.3	2.0	
Output Levels					
V_{OL}	Static Output Level Low	R_L of 1.5 kΩ to 3.6V(3)		0.3	V
V_{OH}	Static Output Level High	R_L of 15 kΩ to V_{SS}(3)	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. It is important to be aware that the DP/DM pins are not 5 V tolerant. As a consequence, in case of a a shortcut with Vbus (typ: 5.0V), the protection diodes of the DP/DM pins will be direct biased . This will not damage the device if not more than 50 mA is sunk for longer than 24 hours but the reliability may be affected.
3. R_L is the load connected on the USB drivers

Figure 41. USB: data signal rise and fall time

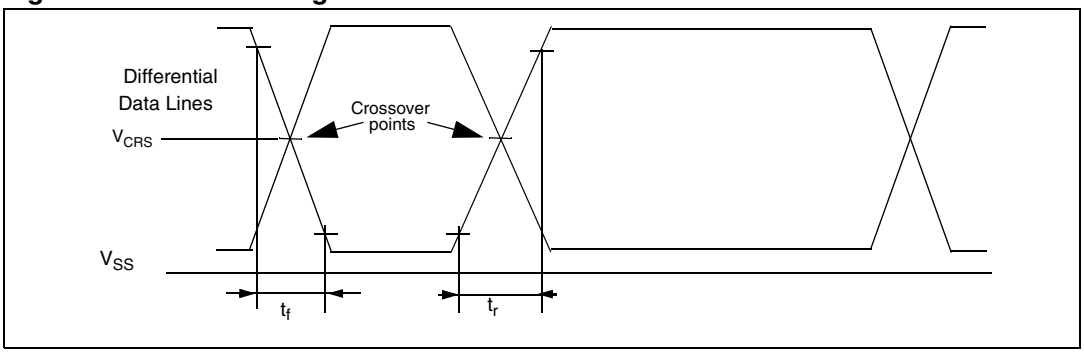


Table 44. USB: Full speed electrical characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
Driver characteristics:					
t_r	Rise time(1)	C_L=50 pF	4	20	ns
t_f	Fall Time1)	C_L=50 pF	4	20	ns

6.3.12 10-bit ADC characteristics

Subject to general operating conditions for V_{DDA_ADC}, f_{PCLK}, and T_A unless otherwise specified.

Table 45. 10-bit ADC characteristics

Symbol	Parameter	Conditions	Min	Typ(1)	Max	Unit
f_{ADC}	ADC clock frequency		0.4		8	MHz
V_{AIN}	Conversion voltage range(2)		V_{SSA_ADC}		V_{DDA_ADC}	V
R_{AIN}	External input impedance(3)(4)				10	kΩ
C_{AIN}	External capacitor on analog input(3)(4)				6.8	pF
I_{lkg}	Induced input leakage current	+400 µA injected on any pin			1	µA
		-400 µA injected on any pin except specific adjacent pins in *Table 46*			1	µA
		-400µA injected on specific adjacent pins in *Table 46*		40		µA
C_{ADC}	Internal sample and hold capacitor			3.5		pF
t_{CAL}	Calibration Time	f_{CK_ADC}=8 MHz	725.25			µs
			5802			$1/f_{ADC}$
t_{CONV}	Total Conversion time (including sampling time)	f_{CK_ADC}=8 MHz	3.75			µs
			30 (11 for sampling + 19 for Successive Approximation)			$1/f_{ADC}$
I_{ADC}		Sunk on V_{DDA_ADC}		3.7		mA

1. Unless otherwise specified, typical data are based on T_A=25°C. They are given only as design guidelines and are not tested.
2. Calibration is needed once after each power-up.
3. $C_{PARASITIC}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (3 pF). A high $C_{PARASITIC}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.
4. Depending on the input signal variation (f_{AIN}), C_{AIN} can be increased for stabilization time and reduced to allow the use of a larger serial resistor (R_{AIN}). It is valid for all f_{ADC} frequencies ≤ 8 MHz.

7.2 Thermal characteristics

The maximum chip junction temperature (T_{Jmax}) must never exceed the values given in *Table 10: General operating conditions on page 34*.

The maximum chip-junction temperature, T_{Jmax}, in degrees Celsius, may be calculated using the following equation:

$$T_{Jmax} = T_{Amax} + (P_{Dmax} \times \Theta_{JA})$$

Where:

- T_{Amax} is the maximum Ambient Temperature in °C,
- Θ_{JA} is the Package Junction-to-Ambient Thermal Resistance, in ° C/W,
- P_{Dmax} is the sum of P_{INTmax} and $P_{I/Omax}$ ($P_{Dmax} = P_{INTmax} + P_{I/Omax}$),
- P_{INTmax} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.
- $P_{I/Omax}$ represents the maximum Power Dissipation on Output Pins.
  Where:
  $P_{I/Omax} = \Sigma (V_{OL}*I_{OL}) + \Sigma((V_{DD}-V_{OH})*I_{OH})$,
  taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 48. Thermal characteristics(1)

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal Resistance Junction-Ambient** LQFP 100 - 14 x 14 mm / 0.5 mm pitch	46	°C/W
Θ_{JA}	**Thermal Resistance Junction-Ambient** LQFP 64 - 10 x 10 mm / 0.5 mm pitch	45	°C/W
Θ_{JA}	**Thermal Resistance Junction-Ambient** LFBGA 64 - 8 x 8 x 1.7mm	58	°C/W
Θ_{JA}	**Thermal Resistance Junction-Ambient** LFBGA 100 - 10 x 10 x 1.7mm	41	°C/W

1. Thermal resistances are based on JEDEC JESD51-2 with 4-layer PCB in a natural convection environment.

7.2.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org